EXTENDED INTERACTION KLYSTRONS FOR TERAHERTZ POWER AMPLIFIERS*

David Chernin, Alex Burke, Igor Chernyavskiy, John Petillo Science Applications International Corp. McLean, VA 22102

Albert Roitman Peter Horoyski, Mark Hyttinen, Richard Dobbs, Dave Berry Communications and Power Industries Georgetown, Ontario, Canada L7G 2J4

Monica Blank Communications and Power Industries, Palo Alto, CA 94304

Khanh Nguyen, Vadim Jabotinsky, Edward Wright, Dean Pershing Beam-Wave Research, Inc. Bethesda, MD 20814

Jeffrey Calame, Baruch Levush Naval Research Laboratory, Washington, DC 20375

Jeffrey Neilson Lexam Research, Redwood City, CA 94062

Todd Gaier, Anders Skalare Jet Propulsion Laboratory, Pasadena, CA 91109

N. Scott Barker, Robert Weikle University of Virginia, Charlottesville, VA 22904

John Booske University of Wisconsin, Madison, WI 53715

Extended Interaction Klystrons have been demonstrated at frequencies up to 218 GHz CW and 229 GHz pulsed. Modern design, fabrication, and measurement technologies show promise of extending their operation into the THz regime. This paper describes the challenges and some novel approaches to the development of EIKs operating terahertz frequencies, while simultaneously meeting demanding requirements for output power, gain, bandwidth, and efficiency.

The main challenges in design include focus and transport of an emittance dominated beam, development of a broadband, high gain circuit, and the minimization of the sensitivity of design to the effects of fabrication and alignment tolerances. The main challenges in fabrication and integration include achieving required component dimensions and alignment within specified tolerances and achieving high quality surface finishes using materials with satisfactory mechanical and thermal properties.

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